

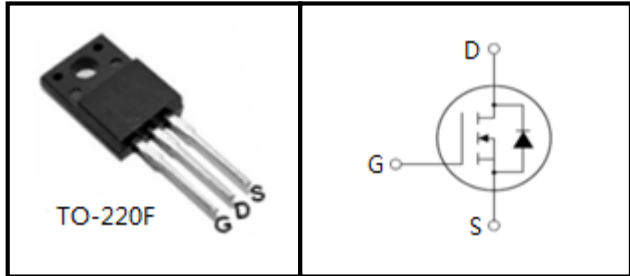
800V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information		
Device	Package	Marking
HF10N80	TO-220F	HF10N80

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted			
Parameter	Symbol	Value	Unit
		TO-220F	
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	800	V
Continuous Drain Current	I_D	10	A
Pulsed Drain Current (note1)	I_{DM}	38	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulse Avalanche Energy (note2)	E_{AS}	281	mJ
Avalanche Current (note1)	I_{AR}	7.5	A
Repetitive Avalanche Energy (note1)	E_{AR}	45	mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	65	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
		TO-220F	
Thermal Resistance, Junction-to-Case	R_{thJC}	1.92	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	800	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 800V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA
		$V_{DS} = 640V, V_{GS} = 0V, T_J = 125^\circ\text{C}$	--	--	100	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{DS} = 250\mu A$	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5.0A$	--	0.8	1.0	Ω
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0MHz$	--	1979	--	pF
Output Capacitance	C_{oss}		--	133	--	
Reverse Transfer Capacitance	C_{rss}		--	53	--	
Total Gate Charge	Q_g	$V_{DD} = 640V, I_D = 10.0A,$ $V_{GS} = 10V$	--	83	--	nC
Gate-Source Charge	Q_{gs}		--	9	--	
Gate-Drain Charge	Q_{gd}		--	49	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 10.0A,$ $R_G = 25\Omega$	--	23	--	ns
Turn-on Rise Time	t_r		--	15	--	
Turn-off Delay Time	$t_{d(off)}$		--	90	--	
Turn-off Fall Time	t_f		--	30	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	10	A
Pulsed Diode Forward Current	I_{SM}		--	--	38	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 10.0A, V_{GS} = 0V$	--	--	1.4	V
Reverse Recovery Time	t_{rr}	$V_{GS} = 0V, I_S = 10.0A,$ $di_F/dt = 100A/\mu s$	--	320	--	ns
Reverse Recovery Charge	Q_{rr}		--	4.2	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = 7.5A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

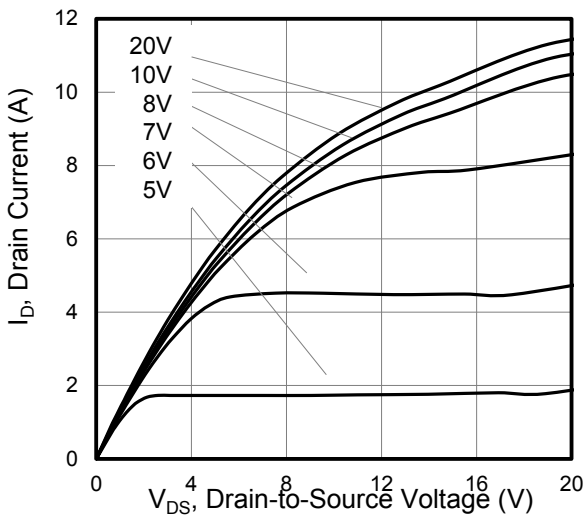


Figure 2. Body Diode Forward Voltage

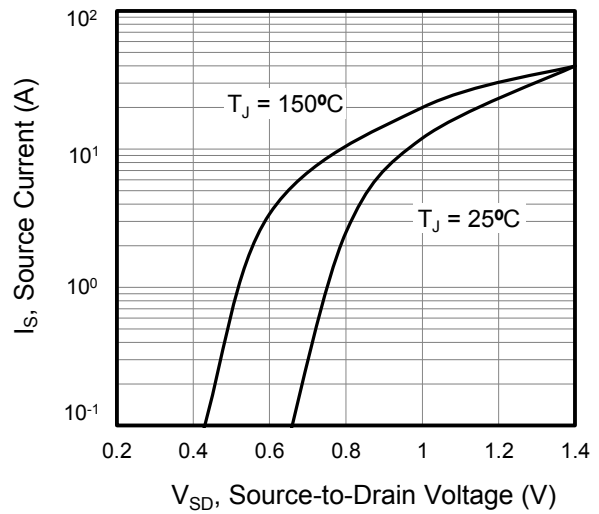


Figure 3. Drain Current vs. Temperature

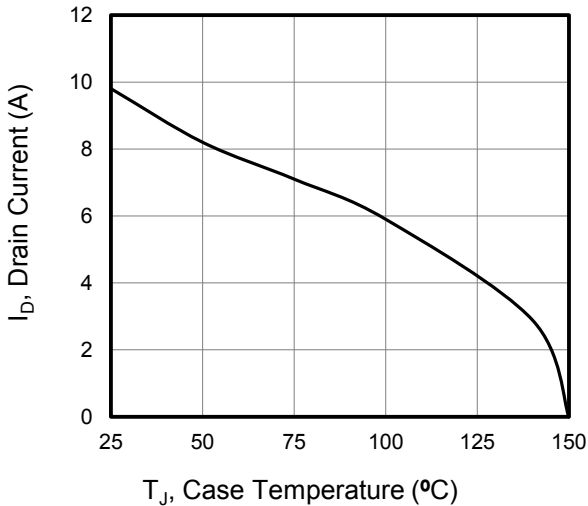


Figure 4. BV_{DSS} Variation vs. Temperature

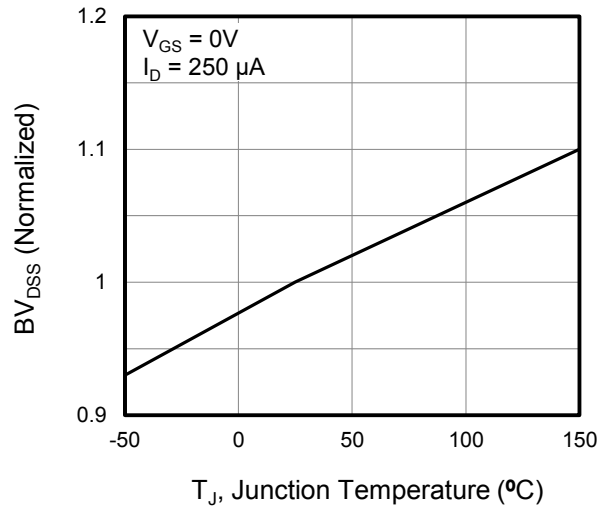


Figure 5. Transfer Characteristics

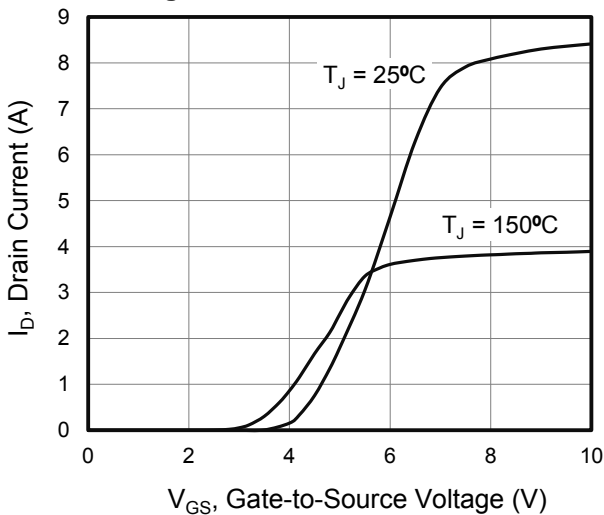
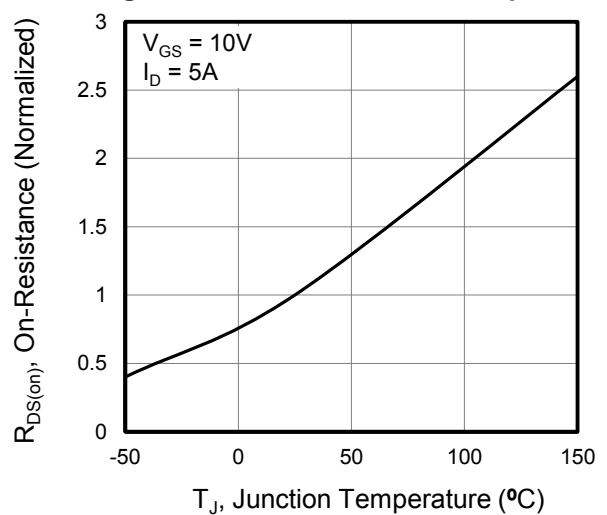


Figure 6. On-Resistance vs. Temperature



Typical Characteristics $T_j = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Capacitance

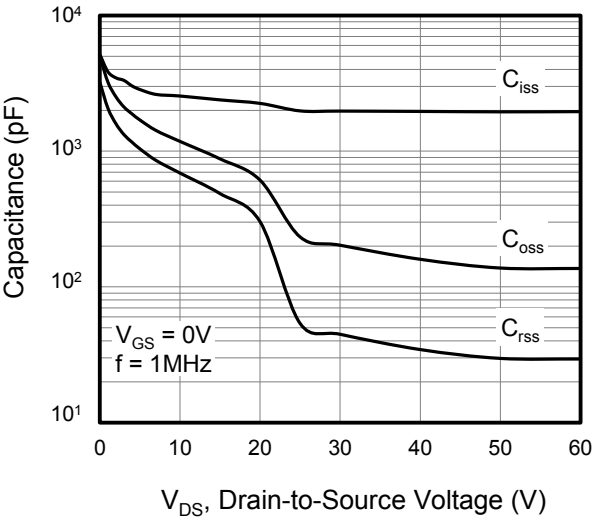


Figure 8. Gate Charge

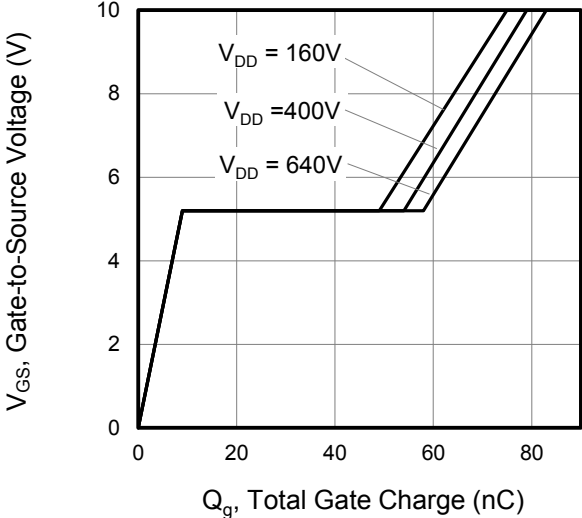


Figure 9. Transient Thermal Impedance

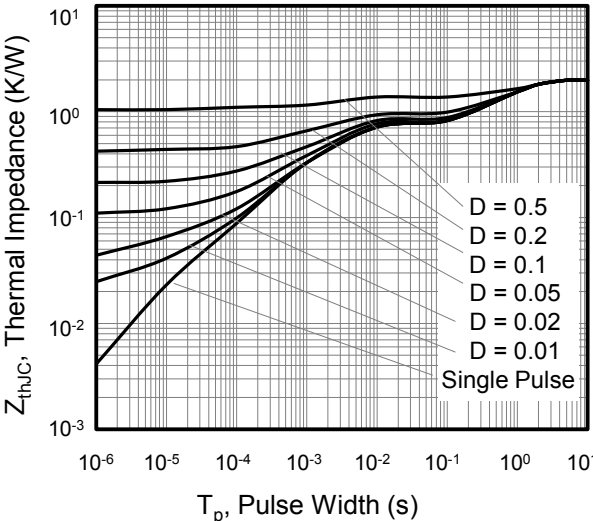


Figure A: Gate Charge Test Circuit and Waveform

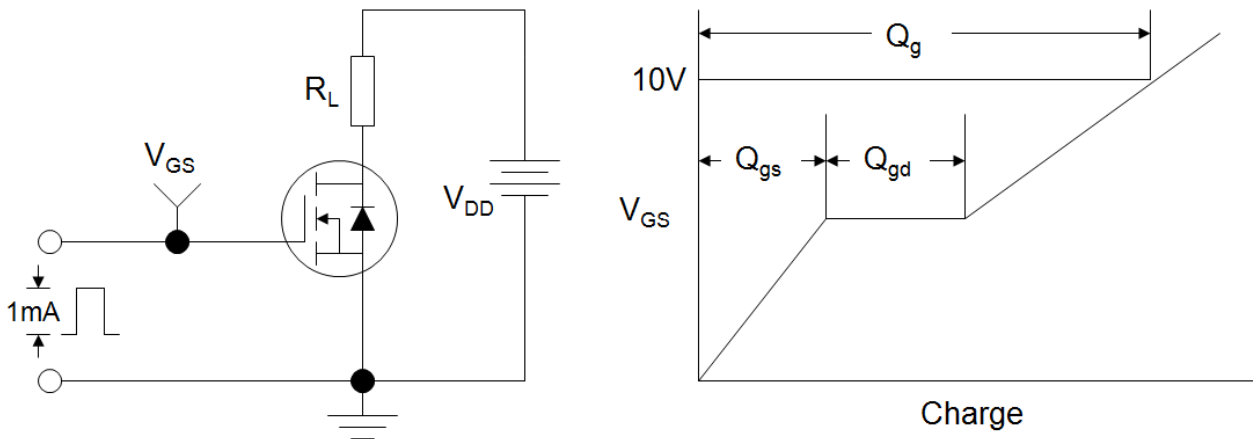


Figure B: Resistive Switching Test Circuit and Waveform

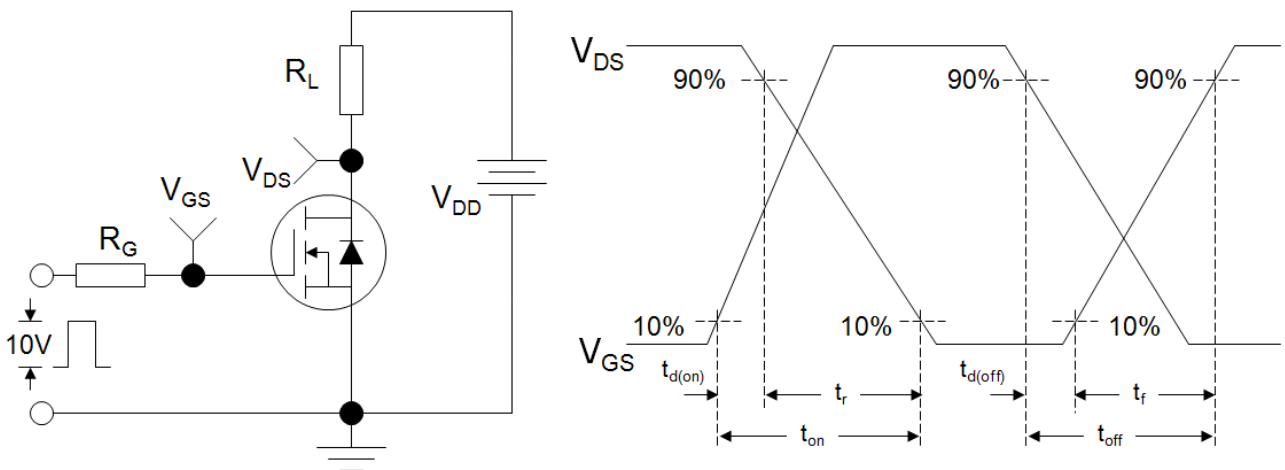
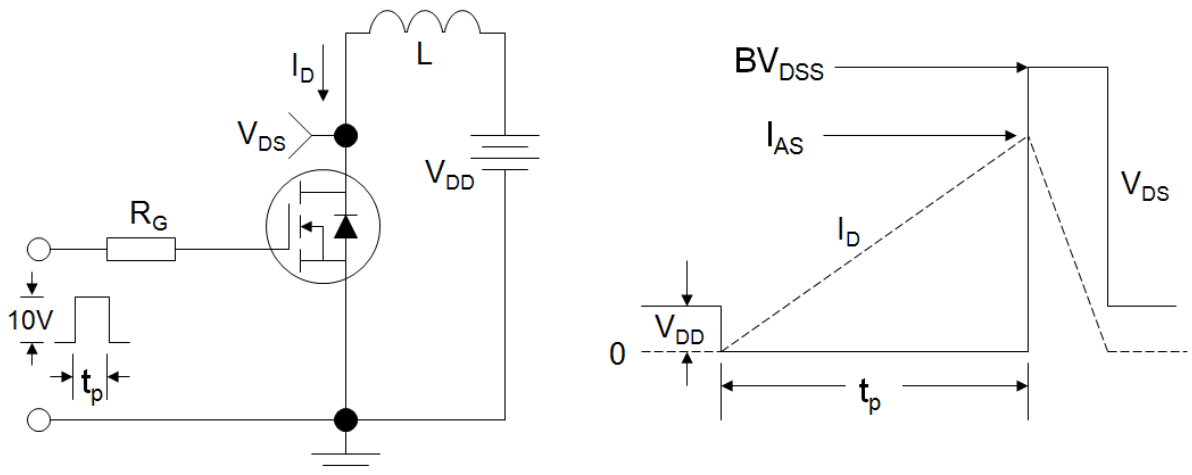
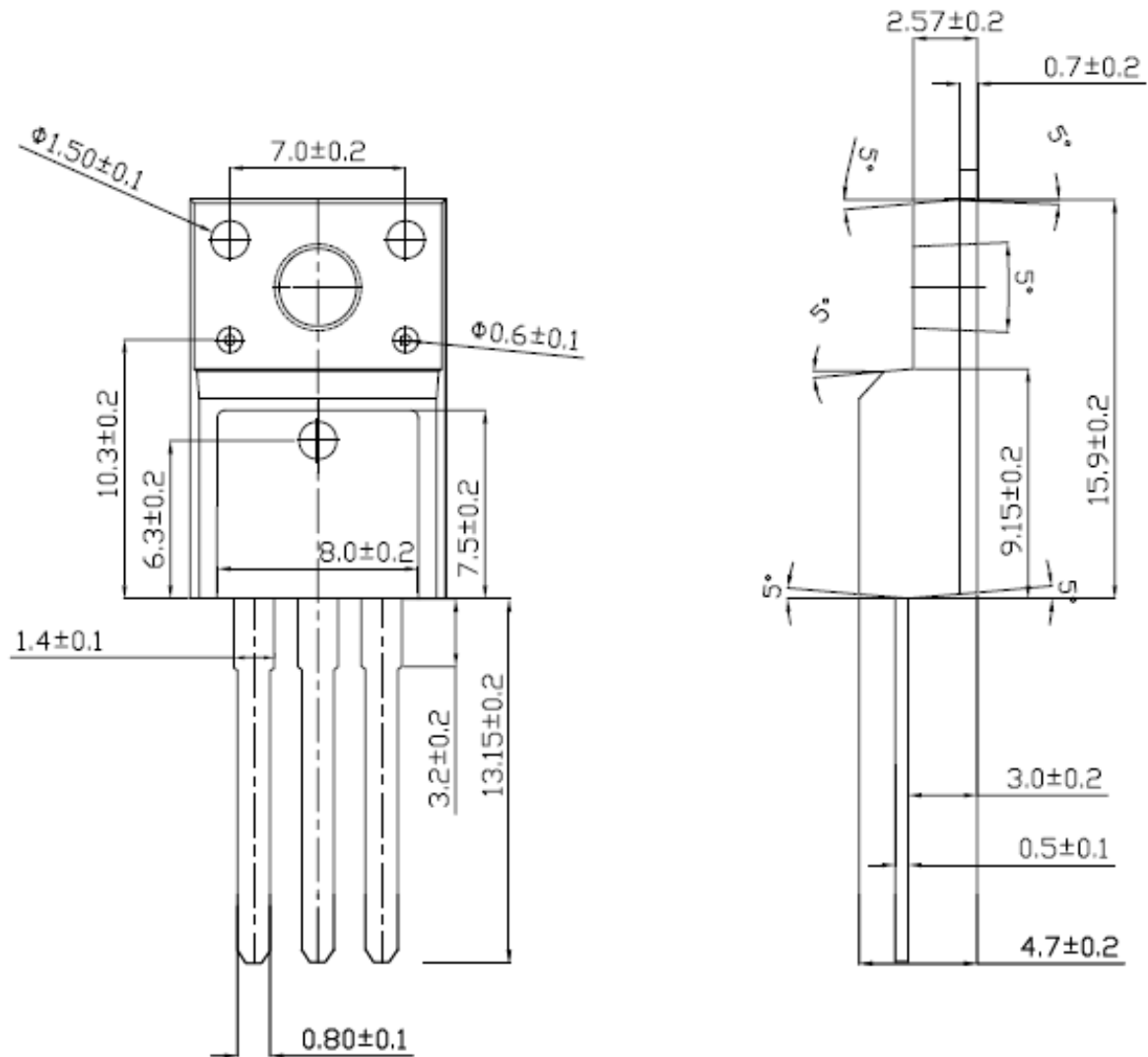


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



TO-220F



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [Haolin](#) manufacturer:

Other Similar products are found below :

[IRFD120](#) [IRFY240C](#) [JANTX2N5237](#) [BUK455-60A/B](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#) [IPS70R2K0CEAKMA1](#)
[SQD23N06-31L-GE3](#) [TK16J60W,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [DMN1053UCP4-7](#) [SQJ469EP-](#)
[T1-GE3](#) [NTE2384](#) [DMC2700UDMQ-7](#) [DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#)
[DMN1006UCA6-7](#) [DMN16M9UCA6-7](#) [STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#)
[DMTH10H4M6SPS-13](#) [DMN2990UFB-7B](#) [IPB80P04P405ATMA2](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [MCQ7328-TP](#) [NTMC083NP10M5L](#)
[NVMFS2D3P04M8LT1G](#) [BXP7N65D](#) [BXP4N65F](#) [AOL1454G](#) [WMJ80N60C4](#) [BXP2N20L](#) [BXP2N65D](#) [BXT1150N10J](#) [BXT1700P06M](#)
[TSM60NB380CP](#) [ROG](#) [RQ7L055BGTCR](#) [DMNH15H110SK3-13](#) [SLF10N65ABV2](#)